High-frequency Amplifier Transistor

Features

- 1) Low collector capacitance (Cob:Typ. 1.3pF)
- 2) Low rbb, high gain and excellent noise characteristics.



Emitter 2. Collector 3. Base
TO-92 Plastic Package
Weight approx. 0.19g

Absolute Maximum Ratings (T_a = 25 °C)

	Symbol	Value	Unit
Collector Base Voltage	V_{CBO}	40	V
Collector Emitter Voltage	V _{CEO}	25	V
Emitter Base Voltage	V_{EBO}	5	V
Collector Current	I _C	50	mA
Power Dissipation	P _{tot}	300	mW
Junction Temperature	T _j	150	°C
Storage Temperature Range	T _S	-55 to +150	°C

G S P FORM A IS AVAILABLE









ST 2SC2058

Characteristics at T_{amb}=25 °C

	Symbol	Min.	Тур.	Max.	Unit
DC Current Gain at V _{CE} =6V, I _C =1mA	h _{FE}	82		180	-
Collector Saturation Voltage at I _C =10mA, I _B =1mA	V _{CEsat}	-	0.1	0.3	V
Collector Cutoff Current at V _{CB} =24V	І _{сво}	-	-	0.5	μ A
Emitter Cutoff Current at V _{EB} =3V	I _{EBO}	-	-	0.5	μ A
Collector Base Breakdown Voltage at I_C =50 μ A	V _{(BR)CBO}	40	-	-	V
Collector Emitter Breakdown Voltage at I _C =1mA	V _{(BR)CEO}	25	-	-	V
Emitter Base Breakdown Voltage at $I_{\rm E}$ =50 μ A	$V_{(BR)EBO}$	5	-	-	V
Transition Frequency at V _{CE} =6V, I _E =-1mA, f=100MHz	f _T	150	300	-	MHz
Output Capacitance at V _{CB} =6V, f=1MHz	Cob	-	1.3	2.2	pF

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